

Wafer Bonder - EVG 501

This bonding system can be used for all wafer bonding processes such as anodic, thermo compression and silicon direct bonding.

Specifications :

- Top & Bottom side heaters up to 550 ° C
- Voltage: Max. 0-2 KV
- Adjustable contact force up to 3.5KN with a resolution of 3.5N
- Bond Current Range: 0-50 mA with a resolution of 200µA.
- Available Bonding Processes: Anodic, thermo compression & silicon direct bonding.



Process Capabilities:

- Substrates Used: Silicon, glass
- Substrate Size: 2", 4"
- Gases Used: GN2